

12. (New) The composite substrate of claim 1, wherein the electrode is a metallic electrode comprising palladium, rhodium, iridium, rhenium, ruthenium, platinum, silver, gold, tantalum, nickel, chromium or titanium.

13. (New) The composite substrate of claim 1, wherein the electrode is a metallic electrode comprising Pd, Pt, Au, Ag or an alloy thereof.

14. (New) The EL device of claim 7, wherein the second electrode is a transparent electrode of ITO or IZO.

15. (New) The EL device of claim 14, wherein said ITO comprises a proportion of SnO_2 to In_2O_3 of from 1 to 20% by weight.

16. (New) The EL device of claim 14, wherein said IZO comprises a proportion of ZnO to In_2O_3 of about 12 to 32% by weight.

17. (New) The EL device of claim 14, wherein the second electrode is silicon-based.

18. (New) The EL device of claim 17, wherein the silicon-based electrode comprises polycrystalline silicon (p-Si), amorphous silicon (a-Si) or single crystal silicon.

19. (New) The EL device of claim 17, wherein said silicon-based electrode comprises a dopant to impart conductivity.

20. (New) The EL device of claim 19, wherein said dopant comprises B, P, As, Sb or Al in an amount of about 0.001 to 5 at.%.

21. (New) The EL device of claim 14, wherein said second electrode has a resistivity of up to $1 \Omega \cdot \text{cm}$.

22. (New) The EL device of claim 21, wherein said second electrode has a resistivity of from about 0.003 to $0.1 \Omega \cdot \text{cm}$.